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General Description

The MAX1778/MAX1880–MAX1885 multiple-output DC-DC converters provide the regulated voltages required by active matrix thin-film transistor (TFT) liquid crystal displays (LCD) in a low-profile TSSOP package. One high-power step-up converter and two low-power charge pumps convert the 2.7V to 5.5V input voltage into three independent output voltages. A built-in linear regulator and VCOM buffer complete the power-supply requirements.

The main step-up converter accurately generates an externally set output voltage up to 13V that can supply the display's row/column drivers. The converter's high switching frequency and current-mode PWM architecture provide fast transient response and allow the use of small low-profile inductors and ceramic capacitors. The low-power BiCMOS control circuitry and internal 14V switch (0.35Ω N-channel MOSFET) enable efficiencies up to 91%.

The dual low-power charge pumps (MAX1778/ MAX1880/MAX1881/MAX1882 only) independently regulate one positive output (VPOS) and one negative output (VNEG). These low-power outputs use external diode and capacitor stages (as many stages as required) to regulate output voltages up to +40V and -40V. A unique control scheme minimizes output ripple as well as capacitor sizes for both charge pumps.

A resistor-programmable, 40mA, low-dropout linear regulator (MAX1778/MAX1881/MAX1883/MAX1884 only) provides preregulation or postregulation for any of the supplies. For higher current applications, an external transistor can be added. Additionally, the VCOM buffer provides a high current output that is ideal for driving the capacitive backplane of TFT LCD panels. The VCOM buffer's output voltage is preset with an internal 50% resistive-divider or can be externally adjusted for other voltages.

The MAX1778/MAX1880–MAX1885 are protected against output undervoltage and thermal overload conditions by a latched fault detection circuit that shuts down the device. All devices are available in the ultrathin TSSOP package (1.1mm max height).

_Applications

TFT LCD Notebook Displays

TFT LCD Desktop Monitor Panels

Features

 500kHz/1MHz Current-Mode PWM Step-Up Regulator
 Up to +13V Main High-Power Output

±1% Accurate High Efficiency (91%)

- Dual Regulated Charge-Pump Outputs (MAX1778/MAX1880–MAX1882 only)
 Up to +40V Positive Charge-Pump Output
 Up to -40V Negative Charge-Pump Output
- Low-Dropout 40mA Linear Regulator (MAX1778/MAX1881/MAX1883/MAX1884 only) Up to +15V LDO Input
- Optional Higher Current with External Transistor
- ♦ 2.7V to 5.5V Input Supply
- Internal Supply Sequencing and Soft-Start
- Power-Ready Output
- Adjustable Fault-Detection Latch
- Thermal Protection (+160°C)
- 0.1µA Shutdown Current
- ♦ 0.7mA IN Quiescent Current
- Ultra-Small External Components
- Thin TSSOP Package (1.1mm max height)

PART **TEMP RANGE** PIN-PACKAGE **MAX1778**EUG -40°C to +85°C 24 TSSOP 24 TSSOP MAX1778EUG+ -40°C to +85°C MAX1880EUG -40°C to +85°C 24 TSSOP MAX1880EUG/V+ -40°C to +85°C 24 TSSOP MAX1881EUG -40°C to +85°C 24 TSSOP MAX1882EUG -40°C to +85°C 24 TSSOP MAX1883EUP -40°C to +85°C 20 TSSOP MAX1884EUP -40°C to +85°C 20 TSSOP MAX1885EUP -40°C to +85°C 20 TSSOP

Ordering Information

+Denotes a lead(Pb)-free/RoHS-compliant package. N denotes an automotive qualified part.

Typical Operating Circuit appears at end of data sheet.

Pin Configurations and Selector Guide appear at end of data sheet.

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maximintegrated.com.

ABSOLUTE MAXIMUM RATINGS

IN, SHDN, TGND, FLTSET to GND	0.3V to +6V
DRVN to GND	0.3V to (V _{SUPN} + 0.3V)
DRVP to GND	0.3V to (V _{SUPP} + 0.3V)
PGND to GND	±0.3V
RDY, SUPB to GND	0.3V to +14V
LX, SUPP, SUPN to PGND	0.3V to +14V
SUPL to GND	0.3V to +18V
LDOOUT to GND	0.3V to (V _{SUPL} + 0.3V)
INTG, REF, FB, FBN, FBP to GND	0.3V to (VIN + 0.3V)
FBL to GND0.3V to the low	ver of (V_{SUPL} + 0.3V) or +6V

SUFOUT, BUF+, BUF- to GND0.3V to (V _{SUPB} + 0.3V)
Continuous Power Dissipation ($T_A = +70^{\circ}C$)
20-Pin TSSOP (derate 10.9mW/°C above +70°C)879mW
24-Pin TSSOP (derate 12.2mW/°C above +70°C)975mW
Derating Temperature Range
MAX1778EUG, MAX1883EUP40°C to +85°C
unction Temperature+150°C
torage Temperature Range65°C to +150°C
ead Temperature (soldering, 10s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, CREF = 0.22\muF, CBUF = 1\muF, TA = 0°C to +85°C. Typical values are at TA = +25°C, unless otherwise noted.)$

PARAMETER	SYMBOL	CONDITIONS			ТҮР	MAX	UNITS
Input Supply Range	VIN			2.7		5.5	V
Input Undervoltage Threshold	V _{UVLO}	V _{IN} rising, 40m	V hysteresis (typ)	2.2	2.4	2.6	V
		Vfb = Vfbp	MAX1778/MAX1880/ MAX1883 (f _{OSC} = 1MHz)		0.7	1	mA
IN Quiescent Supply Current	lin	= 1.5V, V _{FBN} = -0.2V	MAX1881/MAX1882/ MAX1884/MAX1885 (f _{OSC} = 500kHz)		0.6	1	
SUPP Quiescent Current	ISUPP	V _{FBP} = 1.5V	MAX1778/MAX1880 (f _{OSC} = 1MHz)		0.4	0.7	mA
			MAX1881/MAX1882 (f _{OSC} = 500kHz)		0.3	0.5	MA
	I _{SUPN}	V _{FBN} = -0.2V	MAX1778/MAX1880 (f _{OSC} = 1MHz)		0.4	0.7	- mA
SOFN Quescent Current			MAX1881/MAX1882 (f _{OSC} = 500kHz)		0.3	0.5	
IN Shutdown Current		$V_{\overline{SHDN}} = 0, V_{IN}$	= 5V		0.1	10	μA
SUPP Shutdown Current		V <u>SHDN</u> = 0, V _{SUPP} = 13V, MAX1778/MAX1880/MAX1881/MAX1882			0.1	10	μA
SUPN Shutdown Current		V _{SHDN} = 0, V _{SUPN} = 13V, MAX1778/MAX1880/MAX1881/MAX1882			0.1	10	μΑ
SUPL Shutdown Current		$V_{SHDN} = 0, V_{SU}$ MAX1778/MAX		0.1	10	μΑ	
SUPB Shutdown Current		V SHDN = 0, VSU	JPB = 13V		6	13	μA

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, C_{REF} = 0.22\mu$ F, C_{BUF} = 1 μ F, **T_A = 0°C to +85°C**. Typical values are at T_A = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CON	MIN	ТҮР	MAX	UNITS	
MAIN STEP-UP CONVERTER							1
Main Output Voltage Range	VMAIN			VIN		13	V
		Integrator enabled, C	CINTG = 1000pF	1.234	1.247	1.260	
FB Regulation Voltage	VFB	Integrator disabled (I	NTG = REF)	1.220		1.280	V
FB Input Bias Current	I _{FB}	V _{FB} = 1.25V, INTG =	GND	-50		+50	nA
	,	MAX1778/MAX1880/I	MAX1883	0.85	1	1.15	MHz
Operating Frequency	TOSC	MAX1881/MAX1882/	MAX1884/MAX1885	425	500	575	kHz
Oscillator Maximum Duty Cycle				80	85	91	%
		$I_{LX} = 0$ to 200mA,	Integrator enabled, C _{INTG} = 1000pF		0.01		
Load Regulation		V _{MAIN} = 10V	Integrator disabled (INTG = REF)		0.2		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~
Line Regulation					0.1		%/V
Integrator Transconductance					317		μS
LX Switch On-Resistance	R _{LX(ON)}	I _{LX} = 100mA			0.35	0.7	Ω
LX Leakage Current	ILX	$V_{LX} = 13V$			0.01	20	μA
		Phase I = soft-start (1024/f _{OSC})		0.275	0.38	0.5	
	l	Phase II = soft-start (1024/f _{OSC})		0.75		
	LIM	Phase III = soft-start (1024/f _{OSC})			1.12		
		Phase IV = fully on (a	Ifter 3072/f _{OSC})	1.15	1.5	1.85	
Maximum RMS LX Current					1		А
Soft-Start Period	tss	Power-up to the end	of Phase III	3	072 / fos	0	S
ER Fault Trip Lovel		Falling edge, FLTSET = GND		1.07	1.1	1.14	V
		Falling edge, FLTSET	= 1V	0.955	0.99	1.025	v
POSITIVE CHARGE PUMP (MA	X1778/MAX	1880/MAX1881/MAX18	382 only)				
SUPP Input Supply Range	VSUPP			2.7		13	V
Operating Frequency	fCHP				0.5 x f _{OSC}	;	Hz
FBP Regulation Voltage	VFBP			1.2	1.25	1.3	V
FBP Input Bias Current	IFBP	V _{FBP} = 1.5V		-50		+50	nA
DRVP PCH On-Resistance	RPCH(ON)				5	10	Ω
	BNOLION	$V_{FBP} = 1.2V$			2	4	Ω
		$V_{FBP} = 1.3V$		20			kΩ
Maximum RMS DRVP Current					0.1		A
FBP Power-Ready Trip Level		Rising edge		1.09	1.125	1.16	V
FRP Fault Trip Level		Falling edge, FLTSET	= GND	1.08	1.11	1.16	V
FOF FAULTIP Level		Falling edge, FLTSET	0.955	0.99	1.025	v	

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, C_{REF} = 0.22\mu$ F, C_{BUF} = 1 μ F, **T_A = 0°C to +85°C**. Typical values are at T_A = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CON	MIN	ТҮР	МАХ	UNITS		
NEGATIVE CHARGE PUMP (MAX1778/MAX1880/MAX1881/MAX1882 only)								
SUPN Input Supply Range	VSUPN			2.7		13	V	
Operating Frequency	fCHP			(0.5 x fosc	;	Hz	
FBN Regulation Voltage	V _{FBN}			-50	0	+50	mV	
FBN Input Bias Current	I _{FBN}	$V_{FBN} = 0$		-50		+50	nA	
DRVN PCH On-Resistance	RPCH(ON)				5	10	Ω	
	Duouvouv	$V_{FBN} = +50 mV$			2	4	Ω	
DRVIN INCH OII-Resistance	HNCH(ON)	V _{FBN} = -50mV		20			kΩ	
Maximum RMS DRVN Current					0.1		А	
FBN Power-Ready Trip Level		Falling edge		80	125	165	mV	
FBN Fault Trip Level		Rising edge		80	140	190	mV	
LOW-DROPOUT LINEAR REGU	ILATOR (MA	X1778/MAX1881/MAX	(1883/MAX1884 only)					
SUPL Input Supply Range	VSUPL			4.5		15	V	
SUPL Undervoltage Lockout		Rising edge, 50mV hy	ysteresis (typ)	3.8	4	4.3	V	
SUPL Quiescent Current	ISUPL	I _{LDO} = 100μΑ			120	220	μA	
Dropout Voltage (Note 1)	VDROP	LDO is set to	$I_{LDO} = 40 \text{mA}$		130	300	m)/	
Diopout voltage (Note 1)		regulate at 9V	I _{LDO} = 5mA		70		mv	
FBL Regulation Voltage	V _{FBL}	V _{SUPL} = 10V, LDO re I _{LDO} = 15mA	gulating at 9V,	1.235	1.25	1.265	V	
LDO Load Regulation		$V_{SUPL} = 10V, LDO re$ $I_{LDO} = 100\mu A to 40m$	gulating at 9V, A			1.2	%	
LDO Line Regulation		$V_{SUPL} = 4.5V$ to 15V, $I_{LDO} = 15mA$	FBL = LDOOUT,			0.02	%/V	
FBL Input Bias Current	IFBL	$V_{FBL} = 1.25V$		-0.8		+0.8	μA	
LDO Current Limit	ILDOLIM	VSUPL = 10V, VLDOOU	JT = 9V, V _{FBL} = 1.2V	40	130	220	mA	
VCOM BUFFER				•				
SUPB Input Supply Range	VSUPB			4.5		13	V	
SUPB Quiescent Current	ISUPB	V _{SUPB} = 13V			420	850	μA	
BUFOUT Leakage Current				-10		+10	μA	
Power-Supply Rejection Ratio	PSRR	$V_{SUPB} = 4.5V$ to 13V,	V _{CM} = 2.25V	85	98		dB	
Input Common-Mode Voltage Range	Vсм	IV _{OS} I < 10mV		1.2		8.8	V	
Common-Mode Rejection Ratio	CMRR	V _{CM} = 1.2V to 8.8V		75			dB	
Input Bias Current	IBIAS	$V_{CM} = 5V$		-100	-10	+100	nA	
Input Offset Current	los	$V_{CM} = 5V$		-100		+100	nA	
Gain Bandwidth Product	GBW	$C_{BUF} = 1\mu F$			13		kHz	

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, C_{REF} = 0.22\mu$ F, C_{BUF} = 1 μ F, **TA = 0°C to +85°C**. Typical values are at TA = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	COND	TIONS	MIN	TYP	МАХ	UNITS		
			I _{BUFOUT} = 0	4.99		5.01			
Output Voltage	VBUFOUT	BUF+ = GND	$I_{BUFOUT} = \pm 5 mA$	4.97		5.03	V		
			$I_{BUFOUT} = \pm 45 mA$	4.93		5.07			
Input Offset Voltage	Voc	$V_{SUPB} = 4.5V$ to 13V,	$I_{BUFOUT} = \pm 5 mA$	-30		+30	mV		
input onset voltage	103	(V _{SUPB} - 1.2V)	$I_{BUFOUT} = \pm 45 mA$	-70		+70			
Output Voltage Swing High	Voh	$I_{BUFOUT} = -45mA$, ΔV _{OS}	s = 1V	9	9.6		V		
Output Voltage Swing Low	Vol	$I_{BUFOUT} = +45 \text{mA}, \Delta V_{C}$	s = 1V		0.4	1	V		
Peak Buffer Output Current					±150		mA		
BUF+ Dual Mode™ Threshold Voltage		Falling edge, 20mV hys	80	125	170	mV			
REFERENCE	REFERENCE								
Reference Voltage	VREF	-2μA < I _{REF} < 50μA		1.231	1.25	1.269	V		
Reference Undervoltage Threshold				0.9	1.05	1.2	V		
LOGIC SIGNALS									
SHDN Input Low Voltage						0.9	V		
SHDN Input High Voltage				2.1			V		
SHDN Input Current	ISHDN				0.01	1	μA		
ELTSET Input Voltage Bange				0.67 x		0.85 x	V		
				VREF		VREF	v		
FLTSET Threshold Voltage		Rising edge, 25mV hyst	eresis (typ)	80	125	170	mV		
FLTSET Input Current		V _{FLTSET} = 1V			0.1	50	nA		
RDY Output Low Voltage		I _{SINK} = 2mA			0.25	0.5	V		
RDY Output High Leakage		$V_{\overline{RDY}} = 13V$			0.01	1	μA		
Thermal Shutdown		Rising temperature		160		°C			

Dual Mode is a trademark of Maxim Integrated Products, Inc.

ELECTRICAL CHARACTERISTICS

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, C_{REF} = 0.22\mu F, C_{BUF} = 1\mu F, T_{A} = -40^{\circ}C$ to +85°C, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	МАХ	UNITS
Input Supply Range	VIN			2.7	5.5	V
Input Undervoltage Threshold	VUVLO	VIN Rising, 40m	/ hysteresis (typ)	2.2	2.6	V
IN Quiescent Supply		VFB =	MAX1778/MAX1880/ MAX1883 (f _{OSC} = 1MHz)		1	
Current	IN	$V_{FBP} = 1.5V,$ $V_{FBN} = -0.2V$	MAX1881/MAX1882/MAX1884/ MAX1885 (f _{OSC} = 500kHz)		1	ma
			MAX1778/MAX1880 (f _{OSC} = 1MHz)		0.7	
SUPP Quiescent Current	ISUPP	VFBP = 1.5V	MAX1881/MAX1882 (f _{OSC} = 500kHz)		0.5	MA
	1.		MAX1778/MAX1880 (f _{OSC} = 1MHz)		0.7	
SUPN Quiescent Current	ISUPN	$V_{\text{FBN}} = -0.2V$	MAX1881/MAX1882 (f _{OSC} = 500kHz)		0.5	mA
IN Shutdown Current		$V_{\overline{SHDN}} = 0, V_{IN} =$	= 5V		10	μA
SUPP Shutdown Current		$V_{\overline{SHDN}} = 0, V_{SUF}$ MAX1778/MAX1	PP = 13V, 880/MAX1881/MAX1882		10	μA
SUPN Shutdown Current		$V_{\overline{SHDN}} = 0, V_{SUF}$ MAX1778/MAX1	⊳ _N = 13V, 880/MAX1881/MAX1882		10	μA
SUPL Shutdown Current		$V_{\overline{SHDN}} = 0, V_{SUF}$ MAX1778/MAX1	PL = 13V, 881/MAX1883/MAX1884		10	μA
SUPB Shutdown Current		$V_{\overline{SHDN}} = 0, V_{SUF}$	PB = 13V		13	μA
MAIN STEP-UP CONVERTER	3					
Main Output Voltage Range	VMAIN			VIN	13	V
EB Begulation Voltage	Ved	Integrator enabl	ed, C _{INTG} = 1000pF	1.223	1.269	v
	•10	Integrator disab	led (INTG = REF)	1.21	1.29	•
FB Input Bias Current	I _{FB}	$V_{FB} = 1.25V, IN$	TG = GND	-50	+50	nA
Operating Frequency	Fosc	MAX1778/MAX1	880/MAX1883	0.75	1.25	MHz
		MAX1881/MAX1	882/MAX1884/MAX1885	375	625	kHz
Oscillator Maximum Duty Cycle				79	91	%
LX Switch On-Resistance	R _{LX(ON)}	$I_{LX} = 100 \text{mA}$			0.7	Ω
LX Leakage Current	ILX	$V_{LX} = 13V$			20	μA
LX Current Limit		Phase I = soft-st	tart (1024/f _{OSC})	0.275	0.525	А
	. ΓΙΙΛΙ	Phase IV = fully	on (after 3072/f _{OSC})	1.1	2.05	
FB Fault Trip Level		Falling edge, FL	TSET = GND	1.07	1.14	V

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, C_{REF} = 0.22\mu$ F, C_{BUF} = 1 μ F, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS		
POSITIVE CHARGE PUMP (MAX1778/MAX1880/MAX1881/MAX1882 only)							
SUPP Input Supply Range	VSUPP		2.7	13	V		
FBP Regulation Voltage	VFBP		1.2	1.3	V		
FBP Input Bias Current	IFBP	$V_{\text{FBP}} = 1.5 V$	-50	+50	nA		
DRVP PCH On-Resistance	RPCH(ON)			10	Ω		
	Photycon	$V_{\text{FBP}} = 1.2V$		4	Ω		
DRVF NCH OII-RESISIANCE	nnCH(ON)	$V_{\text{FBP}} = 1.3V$	20		kΩ		
FBP Power-Ready Trip Level		Rising edge	1.09	1.16	V		
NEGATIVE CHARGE PUMP ((MAX1778/M	AX1880/MAX1881/MAX1882 only)					
SUPN Input Supply Range	V _{SUPN}		2.7	13	V		
FBN Regulation Voltage	VFBN		-50	+50	mV		
FBN Input Bias Current	IFBN	$V_{\text{FBN}} = 0$	-50	+50	nA		
DRVN PCH On-Resistance	RPCH(ON)			10	Ω		
	Photycom	$V_{FBN} = +50 mV$		4	Ω		
Drvin NCH OII-resistance	nnch(ON)	V _{FBN} = -50mV	20		kΩ		
FBN Power-Ready Trip Level		Falling edge	80	165	mV		
LOW DROPOUT LINEAR RE	GULATOR (N	/IAX1778/MAX1881/MAX1883/MAX1884 only)					
SUPL Input Supply Range	VSUPL		4.5	15	V		
SUPL Undervoltage Lockout		Rising edge, 50mV hysteresis (typ)	3.8	4.3	V		
SUPL Quiescent Current	ISUPL	I _{LDO} = 100μA		240	μA		
Dropout Voltage (Note 1)	VDROP	LDO regulating to 9V, $I_{LDO} = 40 \text{mA}$		330	mV		
FBL Regulation Voltage	V _{FBL}	$V_{SUPL} = 10V$, LDO regulating to 9V, I _{LDO} = 15mA	1.222	1.265	V		
LDO Load Regulation		$V_{SUPL} = 10V$, LDO regulating to 9V, I _{LDO} = 100µA to 40mA		1.2	%		
LDO Line Regulation		$V_{SUPL} = 4.5V$ to 15V, FBL = LDOOUT, I _{LDO} = 15mA		0.02	%/V		
FBL Input Bias Current	IFBL	V _{FBL} = 1.25V	-1.2	+1.2	μA		
LDO Current Limit	ILDOLIM	V _{SUPL} = 10V, V _{LDOOUT} = 9V, V _{FBL} = 1.2V	40	260	mA		
VCOM BUFFER							
SUPB Input Supply Range	VSUPB		4.5	13	V		
SUPB Quiescent Current	ISUPB	V _{SUPB} = 13V		850	μA		
BUFOUT Leakage Current			-10	+10	μA		
Input Common-Mode Voltage	VCM	$ V_{OS} < 10 mV$	1.2	8.8	V		

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = +3.0V, \overline{SHDN} = IN, V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 10V, LDOOUT = FBL, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, C_{REF} = 0.22\mu$ F, C_{BUF} = 1 μ F, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDI	MIN	MAX	UNITS	
Input Bias Current	IBIAS	$V_{CM} = 5V$	-500	+500	nA	
Input Offset Current	los	$V_{CM} = 5V$		-500	+500	nA
			I _{BUFOUT} = 0	4.988	5.012	
Output Voltage	VBUFOUT	BUF+ = GND	$I_{BUFOUT} = \pm 5 mA$	4.97	5.03	V
			$I_{BUFOUT} = \pm 45 mA$	4.93	5.07	
Input Offset Voltage	Vee	$V_{SUPB} = 4.5V \text{ to } 13V$	$I_{BUFOUT} = \pm 5 mA$	-30	+30	m\/
input onset voltage	VUS	(V _{SUPB} - 1.2V)	$I_{BUFOUT} = \pm 45 mA$	-70	+70	IIIV
Output Voltage Swing High	V _{OH}	IBUFOUT = -45mA, ΔV_{OS}	= 1V	9		V
Output Voltage Swing Low	Vol	$I_{BUFOUT} = +45 \text{mA}, \Delta V_{OS}$; = 1V		1	V
BUF+ Dual-Mode Threshold Voltage		Falling edge, 20mV hyste	80	170	mV	
REFERENCE	•					
Reference Voltage	VREF	-2μΑ < I _{REF} < 50μΑ		1.223	1.269	V
Reference Undervoltage Threshold				0.9	1.2	V
LOGIC SIGNALS				•		
SHDN Input Low Voltage					0.9	V
SHDN Input High Voltage				2.1		V
SHDN Input Current	ISHDN				1	μA
FLTSET Input Voltage Range				0.74 x V _{REF}	$0.85 \times V_{REF}$	V
FLTSET Threshold Voltage		Rising edge, 25mV hyste	resis (typ)	80	170	mV
FLTSET Input Current		VFLTSET = 1V			50	nA
RDY Output Low Voltage		$I_{SINK} = 2mA$			0.5	V
RDY Output High Leakage		$V_{\overline{RDY}} = 13V$		1	μA	

Note 1: Dropout voltage is defined as the V_{SUPL} - V_{LDOOUT}, when V_{SUPL} is 100mV below the set value of V_{LDOOUT}.

Note 2: Specifications to -40°C are guaranteed by design, not production tested.

Typical Operating Characteristics

(Circuit of Figure 1, $V_{IN} = +3.3V$, $\overline{SHDN} = IN$, $V_{MAIN} = V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 8V$, BUF = BUFOUT, BUF = FLTSET = TGND = PGND = GND, $T_A = +25^{\circ}C$.)



Typical Operating Characteristics (continued)

(Circuit of Figure 1, VIN = +3.3V, SHDN = IN, VMAIN = VSUPP = VSUPN = VSUPB = VSUPL = 8V, BUF- = BUFOUT, $BUF_{+} = FLTSET = TGND = PGND = GND, T_{A} = +25^{\circ}C.$







STEP-UP CONVERTER LOAD-TRANSIENT RESPONSE



RESPONSE WITHOUT INTEGRATOR 200mA А 0 8.1V В 8.0V 7.9V 1A С 0 40µs/div A. IMAIN = 20mA to 200mA, 200mA/div B. VMAIN = 8V, 100mV/div C. INDUCTOR CURRENT, 1A/div INTG = REF

STEP-UP CONVERTER LOAD-TRANSIENT

STEP-UP CONVERTER LOAD-TRANSIENT RESPONSE (1µs PULSES)



Typical Operating Characteristics (continued)

(Circuit of Figure 1, VIN = +3.3V, SHDN = IN, VMAIN = VSUPP = VSUPN = VSUPB = VSUPL = 8V, BUF- = BUFOUT, $BUF + = FLTSET = TGND = PGND = GND, T_A = +25^{\circ}C.$



A. $V_{MAIN} = 8V$, $I_{MAIN} = 200$ mA, 10mV/div B. $V_{NEG} = -5V$, $I_{NEG} = 10mA$, 20mV/divC. VPOS = 20V, IPOS = 5mA, 20mV/div











- C. POSITIVE CHARGE PUMP = V_{POS} = 20V, R_{LOAD} = 4k Ω , 10V/div
- D. STEP-UP CONVERTER: VMAIN = 8V, RI OAD = 40Q, 10V/div

POWER-UP SEQUENCE (CIRCUIT OF FIGURE 10)



A. RDY, 2V/div B. POSITIVE CHARGE PUMP, VPOS(SYS) = 20V, 10V/div C. STEP-UP CONVERTER: VMAIN(SYS) = 8V, 10V/div D. NEGATIVE CHARGE PUMP, VNEG = -5V, -5V/div

POWER-UP INTO SHORT-CIRCUIT (CIRCUIT OF FIGURE 10)



A. RDY, 2V/div

- B. GATE OF N-CH MOSFET, 5V/div C. STEP-UP CONVERTER, V_{MAIN(START)} = 8V, 5V/div V_{MAIN(SYS)} = GND

E. NEGATIVE CHARGE PUMP: $V_{NEG} = -5V$, $R_{LOAD} = 500\Omega$, 10V/div

Typical Operating Characteristics (continued)

(Circuit of Figure 1, $V_{IN} = +3.3V$, $\overline{SHDN} = IN$, $V_{MAIN} = V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 8V$, BUF = BUFOUT, BUF = FLTSET = TGND = PGND = GND, $T_A = +25^{\circ}C$.)



DROPOUT VOLTAGE vs. LDO LOAD CURRENT (INTERNAL LINEAR REGULATOR)



LDO SUPPLY CURRENT vs. LDO OUTPUT CURRENT (INTERNAL LINEAR REGULATOR)



Typical Operating Characteristics (continued)

(Circuit of Figure 1, $V_{IN} = +3.3V$, $\overline{SHDN} = IN$, $V_{MAIN} = V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 8V$, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, $T_A = +25^{\circ}C$.)



LOAD-TRANSIENT RESPONSE (INTERNAL LINEAR REGULATOR)



A. I_{LD0} = 100 μA TO 40mA, 40mA/div B. V_{LD0} = 5V, 20mV/div V_{SUPL} = V_{LD0} + 500mV

LOAD-TRANSIENT RESPONSE NEAR DROPOUT (INTERNAL LINEAR REGULATOR)



INTERNAL LINEAR-REGULATOR RIPPLE REJECTION



A. V_{LDOOUT} = 5V, I_{LDOOUT} = 40mA, 10mV/div B. V_{MAIN} = V_{SUPL} = 8V, 200mV/div C. I_{MAIN} = 0 TO 750mA, 500mA/div

INTERNAL LINEAR-REGULATOR STARTUP



A. $V_{SHDN} = 0$ TO 2V, 2V/div B. $V_{LDOOUT} = 5V$, $R_{LDOOUT} = 125\Omega$, 2V/div

C. $V_{MAIN} = 8V$, $R_{MAIN} = 40\Omega$, 2V/div

Typical Operating Characteristics (continued)

(Circuit of Figure 1, V_{IN} = +3.3V, SHDN = IN, V_{MAIN} = V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 8V, BUF- = BUFOUT, BUF+ = FLTSET = TGND = PGND = GND, T_A = +25°C.)









EXTERNAL LINEAR-REGULATOR RIPPLE REJECTION AX1778 loc35 2.5V 4.0V 7.8V 1A 0.5A 0 0 10µs/div A. V_{LDO} = 2.5V, I_{LDO} = 200mA, 10mV/div B. VVANU = 5V 200m//div B. VVANU = 2/500 //div



INPUT OFFSET VOLTAGE DEVIATION vs. common-mode voltage



INPUT OFFSET VOLTAGE DEVIATION vs. BUFFER SUPPLY VOLTAGE



Typical Operating Characteristics (continued)

(Circuit of Figure 1, $V_{IN} = +3.3V$, $\overline{SHDN} = IN$, $V_{MAIN} = V_{SUPP} = V_{SUPN} = V_{SUPL} = 8V$, BUF = BUFOUT, BUF = FLTSET = TGND = PGND = GND, $T_A = +25^{\circ}C$.)



A. V_{BUF+} = 3.95V TO 4.05V, 50mV/div B. BUFOUT = BUF-, 50mV/div C_{BUF} = 1 $\mu F,$ V_{SUPB} = 8V

Typical Operating Characteristics (continued)

(Circuit of Figure 1, $V_{IN} = +3.3V$, $\overline{SHDN} = IN$, $V_{MAIN} = V_{SUPP} = V_{SUPN} = V_{SUPB} = V_{SUPL} = 8V$, BUF = BUFOUT, BUF = FLTSET = TGND = PGND = GND, $T_A = +25^{\circ}C$.)



A. $V_{BUF+}=3.50V$ TO 4.50V, 0.5V/div B. BUFOUT = BUF-, 0.5V/div $C_{BUF}=1\mu F,\,V_{SUPB}=8V$



A. I_{BUFOUT} = 200mA PULSES, 200mA/div B. BUFOUT = BUF-, 200mV/div C. V_{MAIN} = 8V, 50mV/div V_{SUPB} = V_{MAIN} , BUF+ = GND, C_{BUF} = 1 μF















Pin Description

PIN					
MAX1778 MAX1881	MAX1880 MAX1882	MAX1883 MAX1884	MAX1885	NAME	FUNCTION
1	1	1	1	FB	Main Step-Up Regulator Feedback Input. Regulates to 1.25V nominal. Connect a resistive divider from the output (V_{MAIN}) to FB to analog ground (GND).
2	2	2	2	INTG	Main Step-Up Integrator Output. When using the integrator, connect 1000pF to analog ground (GND). To disable the integrator, connect INTG to REF.
3	3	3	3	IN	Main Supply Voltage. The supply voltage powers the control circuitry for all the regulators and can range from 2.7V to 5.5V. Bypass with a 0.1μ F capacitor between IN and GND, as close to the pins as possible.
4	4	4	4	BUF+	VCOM Buffer (Operational Transconductance Amplifier) Positive Feedback Input. Connect to GND to select the internal resistive divider that sets the positive input to half the amplifier's supply voltage ($V_{BUF+} = V_{SUPB}/2$).
5	5	5	5	BUF-	VCOM Buffer (Operational Transconductance Amplifier) Negative Feedback Input
6	6	6	6	SUPB	VCOM Buffer (Operational Transconductance Amplifier) Supply Voltage
7	7	7	7	BUFOUT	VCOM Buffer (Operational Transconductance Amplifier) Output
8	8	8	8	GND	Analog Ground. Connect to power ground (PGND) underneath the IC.
9	9	9	9	REF	Internal Reference Bypass Terminal. Connect a 0.22µF ceramic capacitor from REF to analog ground (GND). External load capability up to 50µA.
10	10		_	FBP	Positive Charge-Pump Regulator Feedback Input. Regulates to 1.25V nominal. Connect a resistive divider from the positive charge-pump output (VPOS) to FBP to analog ground (GND).
11	11			FBN	Negative Charge-Pump Regulator Feedback Input. Regulates to 0V nominal. Connect a resistive divider from the negative charge-pump output (V_{NEG}) to FBN to the reference (REF).
12	12	10	10	SHDN	Active-Low Shutdown Control Input. Pull SHDN low to force the controller into shutdown. If unused, connect SHDN to IN for normal operation. A rising edge on SHDN clears the fault latch.
13		11	_	SUPL	Low-Dropout Linear Regulator Input Voltage. Can range from 4.5V to 15V. Bypass with a 1 μ F capacitor to GND (see <i>Capacitor Selection and Regulator Stability</i>). Connect both input pins together externally.

Pin Description (continued)

PIN					
MAX1778 MAX1881	MAX1880 MAX1882	MAX1883 MAX1884	MAX1885	NAME	FUNCTION
14	_	12	_	LDOOUT	Linear Regulator Output. Sources up to 40mA. Bypass to GND with a ceramic capacitor determined by: $C_{LDOOUT} \geq 0.5ms X \left(\frac{I_{LDOOUT(MAX)}}{V_{LDOOUT}}\right)$
15		13		FBL	Voltage Setting Input. Connect a resistive divider from the linear regulator output (V_{LDOOUT}) to FBL to analog ground (GND).
16	16	14	14	FLTSET	Fault Trip-Level Set Input. Connect to a resistive divider between REF and GND to set the main step-up converter's and positive charge pump's fault thresholds between 0.67 x V _{REF} and 0.85 x V _{REF} . Connect to GND for the preset fault threshold (0.9 x V _{REF}).
17	17	_	_	SUPN	Negative Charge-Pump Driver Supply Voltage. Bypass to power ground (PGND) with a $0.1 \mu F$ capacitor.
18	18			DRVN	Negative Charge-Pump Driver Output. Output high level is $V_{\mbox{SUPN}}$ and low level is PGND.
19	19	—	—	SUPP	Positive Charge-Pump Driver Supply Voltage. Bypass to power ground (PGND) with a $0.1\mu F$ capacitor.
20	20	_		DRVP	Positive Charge-Pump Driver Output. Output high level is V_{SUPP} and low level is PGND
21	21	17	17	PGND	Power Ground. Connect to analog ground (GND) underneath the IC.
22	22	18	18	LX	Main Step-Up Regulator Power MOSFET N-Channel Drain. Place output diode and output capacitor as close as possible to PGND.
23	23	19	19	TGND	Must be connected to ground.
24	24	20	20	RDY	Active-Low, Open-Drain Output. Indicates all outputs are ready. On-resistance is 125 Ω (typ).
_	13–15	15, 16	11–13, 15, 16	N.C.	No Connection. Not internally connected.



Figure 1. Typical Application Circuit

Detailed Description

The MAX1778/MAX1880–MAX1885 are highly efficient multiple-output power supplies for thin-film transistor (TFT) liquid crystal display (LCD) applications. The devices contain one high-power step-up converter, two low-power charge pumps, an operational transconductance amplifier (VCOM buffer), and a low-dropout linear regulator. The primary step-up converter uses an internal N-channel MOSFET to provide maximum efficiency and to minimize the number of external components. The output voltage of the main step-up converter (VMAIN) can be set from VIN to 13V with external resistors.

The dual charge pumps (MAX1778/MAX1880–MAX1882 only) independently regulate a positive output (VPOS) and a negative output (VNEG). These low-power outputs use external diode and capacitor stages (as many stages as required) to regulate output voltages from - 40V to +40V. A unique control scheme minimizes output ripple as well as capacitor sizes for both charge pumps.

A resistor-programmable 40mA linear regulator (MAX1778/MAX1881/MAX1883/MAX1884 only) can provide preregulation or postregulation for any of the supplies. For higher current applications, an external transistor can be added.

Additionally, the VCOM buffer provides a high current output that is ideal for driving capacitive loads, such as the backplane of a TFT LCD panel. The positive feedback input features dual-mode operation, allowing this input to be connected to an internal 50% resistivedivider between the buffer's supply voltage and ground, or externally adjusted for other voltages.

Also included in the MAX1778/MAX1880–MAX1885 is a precision 1.25V reference that sources up to 50µA, logic shutdown, soft-start, power-up sequencing, adjustable fault detection, thermal shutdown, and an active-low, open-drain ready output.

Main Step-up Controller

During normal pulse-width modulation (PWM) operation, the MAX1778/MAX1880–MAX1885 main step-up controllers switch at a constant frequency of 500kHz or 1MHz (see the *Selector Guide*), allowing the use of lowprofile inductors and output capacitors. Depending on the input-to-output voltage ratio, the controller regulates the output voltage and controls the power transfer by modulating the duty cycle (D) of each switching cycle:

$$D \approx \frac{V_{MAIN} - V_{IN}}{V_{MAIN}}$$

On the rising edge of the internal clock, the controller sets a flip-flop when the output voltage is too low, which turns on the n-channel MOSFET (Figure 2). The inductor current ramps up linearly, storing energy in a magnetic field. Once the sum of the feedback voltage error amplifier, slope-compensation, and current-feedback signals trip the multi-input comparator, the MOSFET turns off, the flip-flop resets, and the diode (D1) turns on. This forces the current through the inductor to ramp back down, transferring the energy stored in the magnetic field to the output capacitor and load. The MOSFET remains off for the rest of the clock cycle. Changes in the feedback voltage-error signal shift the switch-current trip level, consequently modulating the MOSFET duty cycle.

Under very light loads, an inherent switchover to pulseskipping takes place (Figure 3). When this occurs, the controller skips most of the oscillator pulses in order to reduce the switching frequency and gate charge losses. When pulse-skipping, the step-up controller initiates a new switching cycle only when the output voltage drops too low. The n-channel MOSFET turns on, allowing the inductor current to ramp up until the multi-input comparator trips. Then, the MOSFET turns off and the diode turns on, forcing the inductor current to ramp down. When the inductor current reaches zero, the diode turns off, so the inductor stops conducting current. This forces the threshold between pulse-skipping and PWM operation to coincide with the boundary between continuous and discontinuous inductorcurrent operation:

$$I_{LOAD(CROSSOVER)} \approx \frac{1}{2} \left(\frac{V_{IN}}{V_{MAIN}} \right)^2 \left(\frac{V_{MAIN} - V_{IN}}{f_{OSCL}} \right)$$



Figure 2. Main Step-Up Converter Block Diagram

The switching waveforms appear noisy and asynchronous when light loading causes pulse-skipping operation; this is a normal operating condition that improves light-load efficiency.



Figure 3. Discontinuous-to-Continuous Conduction Crossover Point

Dual Charge-Pump Regulator (MAX1778/ MAX1880–MAX1882 Only)

The MAX1778/MAX1880–MAX1882 controllers contain two independent low-power charge pumps (Figure 4). One charge pump inverts the input voltage and provides a regulated negative output voltage. The second charge pump doubles the input voltage and provides a regulated positive output voltage. The controllers contain internal p-channel and n-channel MOSFETs to control the power transfer. The internal MOSFETs switch at a constant frequency (fCHP = fOSC/2).

Positive Charge Pump

During the first half-cycle, the n-channel MOSFET turns on and charges flying capacitor $C_{X(POS)}$ (Figure 4). This initial charge is controlled by the variable n-channel on-resistance. During the second half-cycle, the n-channel MOSFET turns off and the p-channel MOSFET turns on, level shifting $C_{X(POS)}$ by V_{SUPP} volts. This connects $C_{X(POS)}$ in parallel with the reservoir capacitor $C_{OUT(POS)}$. If the voltage across $C_{OUT(POS)}$ plus a diode drop ($V_{POS} + V_{DIODE}$) is smaller than the level-shifted flying capacitor voltage ($V_{CX(POS)} + V_{SUPP}$), charge flows from $C_{X(POS)}$ to $C_{OUT(POS)}$ until the diode (D3) turns off.



Figure 4. Low-Power Charge Pump Block Diagram

Negative Charge Pump

During the first half-cycle, the p-channel MOSFET turns on, and flying capacitor $C_{X(NEG)}$ charges to V_{SUPN} minus a diode drop (Figure 4). During the second half-cycle, the p-channel MOSFET turns off, and the n-channel MOSFET turns on, level shifting $C_{X(NEG)}$. This connects $C_{X(NEG)}$ in parallel with reservoir capacitor $C_{OUT(NEG)}$. If the voltage across $C_{OUT(NEG)}$ minus a diode drop is greater than the voltage across $C_{X(NEG)}$, charge flows from $C_{OUT(NEG)}$ to $C_{X(NEG)}$ until the diode (D5) turns off. The amount of charge transferred to the output is controlled by the variable n-channel on-resistance.

Low-Dropout Linear Regulator (MAX1778/ MAX1881/MAX1883/MAX1884 Only)

The MAX1778/MAX1881/MAX1883/MAX1884 contain a low-dropout linear regulator (Figure 5) that uses an internal PNP pass transistor (QP) to supply loads up to 40mA. As illustrated in Figure 5, the 1.25V reference is connected to the error amplifier, which compares this reference with the feedback voltage and amplifies the difference. If the feedback voltage is higher than the reference voltage, the controller lowers the base current of QP, which reduces the amount of current to the output. If the feedback voltage is too low, the device increases the pass transistor base current, which allows more current to pass to the output and increases the output voltage. However, the linear regulator also includes an output current limit to protect the internal pass transistor against short circuits.

The low-dropout linear regulator monitors and controls the pass transistor's base current, limiting the output current to 130mA (typ). In conjunction with the thermal overload protection, this current limit protects the output, allowing it to be shorted to ground for an indefinite period of time without damaging the part.

VCOM Buffer

The MAX1778/MAX1880–MAX1885 include a VCOM buffer, which uses an operational transconductance amplifier (OTA) to provide a current output that is ideal for driving capacitive loads, such as the backplane of a TFT LCD panel. The unity-gain bandwidth of this current-output buffer is:

$GBW = gm/C_{OUT}$

where gm is the amplifier's transconductance. The bandwidth is inversely proportional to the output capacitor, so large capacitive loads improve stability; however, lower bandwidth decreases the buffer's transient response time. To improve the transient response



Figure 5. Low-Dropout Linear Regulator Block Diagram



Figure 6. VCOM Buffer Block Diagram

times, the amplifier's transconductance increases as the output current increases (see the *Typical Operating Characteristics*).

The VCOM buffer's positive feedback input features dual mode operation. The buffer's output voltage can be internally set by a 50% resistive divider connected to the buffer's supply voltage (SUPB), or the output voltage can be externally adjusted for other voltages.

Shutdown (SHDN)

A logic-low level on SHDN shuts down all of the converters and the reference. When shut down, the supply current drops to 0.1µA to maximize battery life, and the reference is pulled to ground. The output capacitance, feedback resistors, and load current determine the rate at which each output voltage decays. A logic-level high on SHDN power activates the MAX1778/MAX1880–MAX1885 (see the *Power-Up Sequencing* section). Do not leave SHDN floating. If unused, connect SHDN to IN. A logic-level transition on SHDN clears the fault latch.

Power-Up Sequencing

Upon power-up or exiting shutdown, the MAX1778/ MAX1880–MAX1885 start a power-up sequence. First, the reference powers up. Then, the main DC-DC stepup converter powers up with soft-start enabled. The linear regulator powers up at the same time as the main step-up converter; however, the power sequence and

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ready output signal are not affected by the regulation of the linear regulator. While the main step-up converter powers up, the output of the PWM comparator remains low (Figure 2), and the step-up converter charges the output capacitors, limited only by the maximum duty cycle and current-limit comparator. When the step-up converter approaches its nominal regulation value and the PWM comparator's output changes states for the first time, the negative charge pump turns on. When the negative output voltage reaches approximately 90% of its nominal value ($V_{FBN} < 110 \text{mV}$), the positive charge pump starts up. Finally, when the positive output voltage reaches 90% of its nominal value ($V_{FBP} > 1.125V$), the active-low ready signal (RDY) goes low (see the Power Ready section), and the VCOM buffer powers up. The MAX1883–MAX1885 do not contain the charge pumps, but the power-up sequence still contains the charge pumps' startup logic, which appears as a delay (2 × 4096/fOSC) between the step-up converter reaching regulation and when the ready signal and VCOM buffer are activated.

Soft-Start

For the main step-up regulator, soft-start allows a gradual increase of the current-limit level during startup to reduce input surge currents. The MAX1778/MAX1880– MAX1885 divide the soft-start period into four phases. During the first phase, the controller limits the current limit to only 0.38A (see the *Electrical Characteristics*), approximately a quarter of the maximum current limit

(I_{LX(MAX)}). If the output does not reach regulation within 1ms, soft-start enters phase II, and the current limit is increased by another 25%. This process is repeated for phase III. The maximum 1.5A (typ) current limit is reached within 3072 clock cycles or when the output reaches regulation, whichever occurs first (see the startup waveforms in the *Typical Operating Characteristics*).

For the charge pumps (MAX1778/MAX1880–MAX1882 only), soft-start is achieved by controlling the rate of rise of the output voltage. Both charge-pump output voltages are controlled to be in regulation within 4096 clock cycles, irregardless of output capacitance and load, limited only by the charge pump's output impedance. Although the MAX1883–MAX1885 controllers do not include the charge pumps, the soft-start logic still contains the 4096 clock cycle startup periods for both charge pumps.

Fault Trip Level (FLTSET)

The MAX1778/MAX1880–MAX1885 feature dual-mode operation to allow operation with either a preset fault trip level or an adjustable trip level for the step-up converter and positive charge-pump outputs. Connect FLTSET to GND to select the preset $0.9 \times V_{REF}$ fault threshold. The fault trip level can also be adjusted by connecting a voltage-divider from REF to FLTSET (Figure 8). For greatest accuracy, the total load on the reference (including current through the negative charge-pump feedback resistors) should not exceed 50µA so that V_{REF} is guaranteed to be in regulation (see the *Electrical Characteristics*). Therefore, select R10 in the 100k Ω to 1M Ω range, and calculate R9 with the following equation:

R9 = R10 [(VREF/VFLTSET) - 1]

where $V_{REF} = 1.25V$, and V_{FLTSET} can range from 0.67 x V_{REF} to 0.85 x V_{REF} . FLTSET's input bias current has a maximum value of 50nA. For 1% error, the current through R10 should be at least 100 times the FLTSET input bias current (IFLTSET).

Fault Condition

Once RDY is low, if the output of the main regulator or either low-power charge pump falls below its fault detection threshold, or if the input drops below its undervoltage threshold, then RDY goes high impedance and all outputs shut down; however, the reference remains active. After removing the fault condition, toggle shutdown (below 0.8V) or cycle the input voltage (below 0.2V) to clear the fault latch and reactivate the device.

The reference fault threshold is 1.05V. For the step-up converter and positive charge-pump, the fault trip level is

set by FLTSET (see the *Fault Trip Level (FLTSET*) section). For the negative charge pump, the fault threshold measured at the charge-pump's feedback input (FBN) is 140mV (typ).

Power Ready (RDY)

 $\overline{\text{RDY}}$ is an open-drain output. When the power-up sequence for the main step-up converter and low-power charge pumps has properly completed, the 14V MOSFET turns on and pulls $\overline{\text{RDY}}$ low with a 125 Ω (typ) on-resistance. If a fault is detected on any of these three outputs, the internal open-drain MOSFET appears as a high impedance. Connect a 100k Ω pullup resistor between $\overline{\text{RDY}}$ and IN for a logic-level output.

Voltage Reference (REF)

The voltage at REF is nominally 1.25V. The reference can source up to 50µA with good load regulation (see the *Typical Operating Characteristics*). Connect a 0.22µF ceramic bypass capacitor between REF and GND.

Thermal-Overload Protection

Thermal-overload protection limits total power dissipation in the MAX1778/MAX1880–MAX1885. When the junction temperature exceeds $T_J = +160^{\circ}$ C, a thermal sensor activates the fault protection, which shuts down the controller, allowing the IC to cool. Once the device cools down by 15°C, toggle shutdown (below 0.8V) or cycle the input voltage (below 0.2V) to clear the fault latch and reactivate the controller. Thermal-overload protection protects the controller in the event of fault conditions. For continuous operation, do not exceed the absolute maximum junction-temperature rating of $T_J = +150^{\circ}$ C.

Operating Region and Power Dissipation

The MAX1778/MAX1880–MAX1885s' maximum power dissipation depends on the thermal resistance of the IC package and circuit board, the temperature difference between the die junction and ambient air, and the rate of any airflow. The power dissipated in the device depends on the operating conditions of each regulator and the buffer.

The step-up controller dissipates power across the internal n-channel MOSFET as the controller ramps up the inductor current. In continuous conduction, the power dissipated internally can be approximated by:

$$\begin{array}{ll} \mathsf{P}_{\mathsf{STEP}-\mathsf{UP}} &\approx \left[\left(\frac{\mathsf{I}_{\mathsf{MAIN}}\mathsf{V}_{\mathsf{MAIN}}}{\mathsf{V}_{\mathsf{N}}} \right)^2 \ + \ \frac{1}{12} \left(\frac{\mathsf{V}_{\mathsf{IN}}\mathsf{D}}{\mathsf{f}_{\mathsf{OSC}}\mathsf{L}} \right)^2 \right] \\ & \times \ \mathsf{R}_{\mathsf{DS}(\mathsf{ON})}\mathsf{D} \end{array}$$

where I_{MAIN} includes the primary load current and the input supply currents for the charge pumps (see the *Charge-Pump Input Power and Efficiency Considerations* section), linear regulator, and VCOM buffer.

The linear regulator generates an output voltage by dissipating power across an internal pass transistor, so the power dissipation is simply the load current times the input-to-output voltage differential:

$$P_{LDO(INT)} = I_{LDO}(V_{SUPL} - V_{LDO})$$

When driving an external transistor, the internal linear regulator provides the base drive current. Depending on the external transistor's current gain (β) and the maximum load current, the power dissipated by the internal linear regulator can still be significant:

$$P_{LDO(INT)} = \frac{I_{LDO}}{\beta} [V_{SUPL} - (V_{LDO} + 0.7V)]$$
$$= I_{LDOOUT} (V_{SUPL} - V_{LDOOUT})$$

The charge pumps provide regulated output voltages by dissipating power in the low-side n-channel MOSFET, so they could be modeled as linear regulators followed by unregulated charge pumps. Therefore, their power dissipation is similar to a linear regulator:

$$P_{NEG} = I_{NEG} [(V_{SUPN} - 2V_{DIODE})N - V_{NEG}]$$

$$P_{POS} = I_{POS} [(V_{SUPP} - 2V_{DIODE})N + V_{SUPD} - V_{POS}]$$

where N is the number of charge-pump stages, VDIODE is the diodes' forward voltage, and VSUPD is the positive charge-pump diode supply (Figure 4).

The VCOM buffer's power dissipation depends on the capacitive load (C_{LOAD}) being driven, the peak-to-peak voltage change (VP-P) across the load, and the load's switching rate:

$$P_{BUF} = V_{P-P}C_{LOAD} I_{LOAD} V_{SUPB}$$

To find the total power dissipated in the device, the power dissipated by each regulator and the buffer must be added together:

$$P_{TOTAL} = P_{STEP-UP} + P_{LDO(INT)} + P_{NEG} + P_{POS} + P_{BUF}$$

The maximum allowed power dissipation is 975mW (24pin TSSOP)/879mW (20-pin TSSOP) or:

Maxim Integrated

 $P_{MAX} = (T_{J(MAX)} - T_{A})/(\theta_{JB} + \theta_{BA})$

where T_J - T_A is the temperature difference between the controller's junction and the surrounding air, θ_{JB} (or θ_{JC}) is the thermal resistance of the package to the board, and θ_{BA} is the thermal resistance from the PCB to the surrounding air.

Design Procedure

Main Step-Up Converter

Output-Voltage Selection

Adjust the output voltage by connecting a voltagedivider from the output (VMAIN) to FB to GND (see the *Typical Operating Circuit*). Select R2 in the 10k Ω to 50k Ω range. Calculate R1 with the following equations:

$$R1 = R2 [(V_{MAIN}/V_{REF}) - 1]$$

where $V_{REF} = 1.25V$. VMAIN can range from VIN to 13V.

Inductor Selection

Inductor selection depends upon the minimum required inductance value, saturation rating, series resistance, and size. These factors influence the converter's efficiency, maximum output load capability, transient response time, and output-voltage ripple. For most applications, values between 4.7µH and 22µH work best with the controller's switching frequency (Tables 1 and 2).

The inductor value depends on the maximum output load the application must support, input voltage, output voltage, and switching frequency. With high inductor values, the MAX1778/MAX1880-MAX1885 source higher output currents, have less output ripple, and enter continuous conduction operation with lighter loads; however, the circuit's transient response time is slower. On the other hand, low-value inductors respond faster to transients, remain in discontinuous conduction operation, and typically offer smaller physical size for a given series resistance and current rating. The equations provided here include a constant LIR, which is the ratio of the peak-to-peak AC inductor current to the average DC inductor current. For a good compromise between the size of the inductor, power loss, and output-voltage ripple, select an LIR of 0.3 to 0.5. The inductance value is then given by:

$$L_{MIN} = \left(\frac{V_{IN(MIN)}}{V_{MAIN}}\right)^{2} \left(\frac{V_{MAIN} - V_{IN(MIN)}}{I_{MAIN(MAX)}f_{OSC}}\right) \left(\frac{1}{LIR}\right) \eta$$